

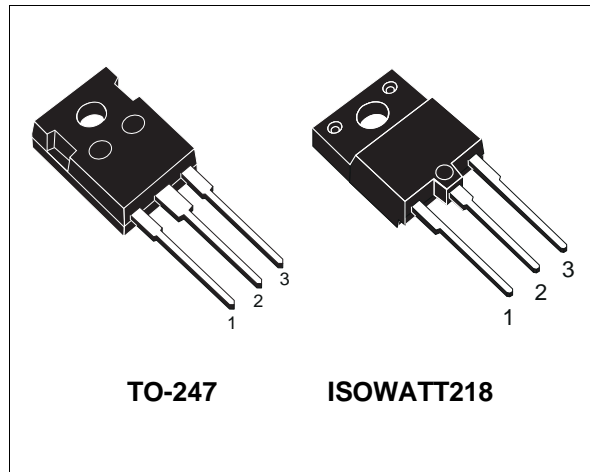
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTORS

TYPE	V _{DSS}	R _{DS(on)}	I _D
STW7NA100	1000 V	< 1.7 Ω	7 A
STH7NA100FI	1000 V	< 1.7 Ω	4.3 A

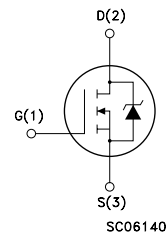
- TYPICAL R_{DS(on)} = 1.45 Ω
- ± 30V GATE TO SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- GATE CHARGE MINIMISED
- REDUCED THRESHOLD VOLTAGE SPREAD

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLY (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STW7NA100	STH7NA100FI	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	1000		V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	1000		V
V _{GS}	Gate-source Voltage	± 30		V
I _D	Drain Current (continuous) at T _c = 25 °C	7	4.3	A
I _D	Drain Current (continuous) at T _c = 100 °C	4.4	2.7	A
I _{DM} (●)	Drain Current (pulsed)	28	28	A
P _{tot}	Total Dissipation at T _c = 25 °C	190	70	W
	Derating Factor	1.52	0.56	W/°C
V _{ISO}	Insulation Withstand Voltage (DC)	—	4000	V
T _{stg}	Storage Temperature	-65 to 150		°C
T _j	Max. Operating Junction Temperature	150		°C

(●) Pulse width limited by safe operating area

STW7NA100-STH7NA100FI

THERMAL DATA

		TO-247	ISOWATT218		
R _{thj-case}	Thermal Resistance Junction-case	Max	0.65	1.78	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	30		°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.1		°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%)	7	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	800	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	1000			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _c = 100 °C			50 250	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 30 V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2.25	3	3.75	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 3.5 A		1.45	1.7	Ω Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	7			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 3.5 A	5	7		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		3170	4100	pF
C _{oss}	Output Capacitance			270	351	pF
C _{rss}	Reverse Transfer Capacitance			76	99	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 500\text{ V}$ $I_D =$		28	40	ns
t_r	Rise Time	3.5 A $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		19	27	ns
Q_g	Total Gate Charge	$V_{DD} = 800\text{ V}$ $I_D = 7\text{ A}$ $V_{GS} = 10\text{ V}$		125	150	nC
Q_{gs}	Gate-Source Charge			17		nC
Q_{gd}	Gate-Drain Charge			58		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 800\text{ V}$ $I_D = 7\text{ A}$		35	50	ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		15	21	ns
t_c	Cross-over Time			55	77	ns

SOURCE DRAIN DIODE

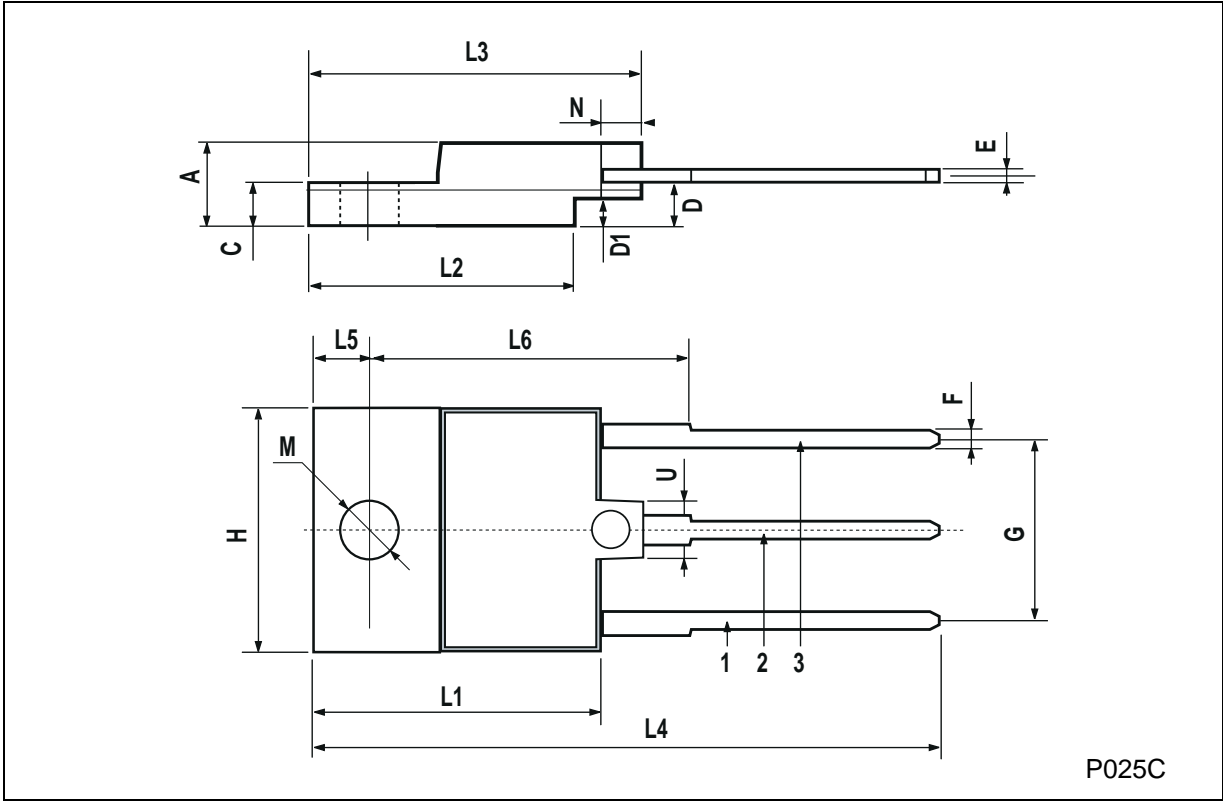
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				7	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				28	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 7\text{ A}$ $V_{GS} = 0$			1.6	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 7\text{ A}$ $V_{DD} = 100\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$ $T_j = 150\text{ }^\circ\text{C}$		835		ns
Q_{rr}	Reverse Recovery Charge			14		μC
I_{RRM}	Reverse Recovery Current			33		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

ISOWATT218 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.210		0.222
C	3.3		3.8	0.130		0.149
D	2.9		3.1	0.114		0.122
D1	1.88		2.08	0.074		0.081
E	0.75		1	0.029		0.039
F	1.05		1.25	0.041		0.049
G	10.8		11.2	0.425		0.441
H	15.8		16.2	0.622		0.637
L1	20.8		21.2	0.818		0.834
L2	19.1		19.9	0.752		0.783
L3	22.8		23.6	0.897		0.929
L4	40.5		42.5	1.594		1.673
L5	4.85		5.25	0.190		0.206
L6	20.25		20.75	0.797		0.817
M	3.5		3.7	0.137		0.145
N	2.1		2.3	0.082		0.090
U		4.6			0.181	



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